VS-ST730CL Series

Vishay Semiconductors



Phase Control Thyristors (Hockey PUK Version), 990 A



B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS						
I _{T(AV)}	990 A					
V _{DRM} /V _{RRM}	800 V, 1200 V, 1400 V, 1600 V, 1800 V, 2000 V					
V _{TM}	1.62 V					
I _{GT}	100 mA					
TJ	-40 °C to +125 °C					
Package	B-PUK (TO-200AC)					
Circuit configuration	Single SCR					

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
		990	А				
I _{T(AV)}	T _{hs}	55	C°				
		2000	A				
IT(RMS)	T _{hs}	25	C°				
	50 Hz	17 800	А				
ITSM	60 Hz	18 700	A				
l ² t	50 Hz	1591	kA ² s				
1-1	60 Hz	1452	KA-S				
V _{DRM} /V _{RRM}		800 to 2000	V				
t _q	Typical	150	μs				
TJ		-40 to 125	C°				

VOLTAGE RATINGS									
TYPE VOLTAGE NUMBER CODE		V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM} MAXIMUM AT T_J = T_J MAXIMUM mA$					
	08	800	900						
	12	1200	1300						
	14	1400	1500	80					
VS-ST730CL	16	1600	1700	00					
	18	1800	1900						
	20	2000	2100						

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1

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COMPLIANT

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ABSOLUTE MAXIMUM RATING	5					
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current	L	180° condu	ction, half sine v	wave	990 (375)	Α
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink temp	erature double side cooled	2000	
		t = 10 ms	No voltage		17 800	
Maximum peak, one-cycle	L	t = 8.3 ms	reapplied		18 700	А
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		15 000	kA ² s
		t = 8.3 ms	reapplied	Sinusoidal half wave,	15 700	
		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	1591	
Maximum I ² t for fusing	l ² t	t = 8.3 ms			1452	
Maximum tion fusing		t = 10 ms	100 % V _{RRM}		1125	
		t = 8.3 ms	reapplied		1027	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10) ms, no voltage	e reapplied	15 910	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x \ I_{T(AV)} < I < \pi \ x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.98	v
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$		1.12	v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T _J = T _J maximum		0.32	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$		0.27	1115.2	
Maximum on-state voltage	V_{TM}	$I_{pk} = 2000 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$		1.62	V	
Maximum holding current	Ι _Η	T 25 °C	anode supply 1	2 V resistive load	600	mA
Typical latching current	١ _L	1 _J = 25 °C,	anoue supply 1		1000	

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \leq 1 \; \mu s$ $T_J = T_J$ maximum, anode voltage $\leq 80 \; \% \; V_{DRM}$	1000	A/µs			
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.0				
Typical turn-off time	tq	I_{TM} = 750 A, T_J = T_J maximum, dl/dt = 60 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	150	μs			

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs		
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$I_1 = I_1 \prod_{i=1}^{n} \prod_{j=1}^{n} \prod_{j=1}^{n} \prod_{j=1}^{n} \prod_{i=1}^{n} \prod_{j=1}^{n} \prod_{j=1$		mA		

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TRIGGERING						
PABAMETER	SYMBOL	те	ST CONDITIONS	VAL	UES	UNITS
		ST CONDITIONS	Тур.	Max.	UNITS	
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	$t_p \le 5 ms$	10	0.0	w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 ms$	3	.0	А
Maximum peak positive gate voltage	$+ V_{GM}$		+ < 5 mg	20		v
Maximum peak negative gate voltage	- V _{GM}	ij = ij maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms			
		T _J = -40 °C		200	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate	100	200	mA
		T _J = 125 °C	trigger/ current/voltage are the lowest	50	-	
		T _J = -40 °C	value which will trigger all units		-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 V anode to cathode applied	1.8	3.0	V
		T _J = 125 °C		1.1	-	
DC gate current not to trigger	I _{GD}		Maximum gate current/voltage not to trigger is the maximum	1	0	mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J$ maximum	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	℃		
Maximum storage temperature range	T _{Stg}		-40 to 150			
Maximum thermal registerion, junction to heataink	В	DC operation single side cooled	0.073			
Maximum thermal resistance, junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.031	K/W		
Maximum thermal registeres, sees to besteink	R _{thC-hs}	DC operation single side cooled	0.011	- r√ vv		
Maximum thermal resistance, case to heatsink		DC operation double side cooled	0.006			
Mounting force, ± 10 %			14 700 (1500)	N (kg)		
Approximate weight			255	g		
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-	200AC)		

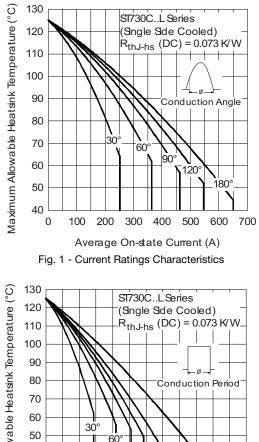
CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULAR	R CONDUCTION		UNITS		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS		
180°	0.009	0.009	0.006	0.006				
120°	0.011	0.011	0.010	0.011				
90°	0.014	0.014	0.015	0.015	$T_J = T_J maximum$	K/W		
60°	0.020	0.020	0.021	0.021				
30°	0.036	0.036	0.036	0.036				

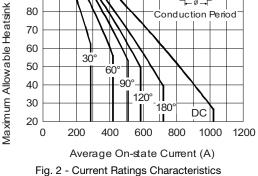
Note

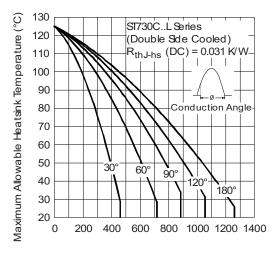
The table above shows the increment of thermal resistance RthJ-hs when devices operate at different conduction angles than DC ٠

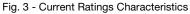
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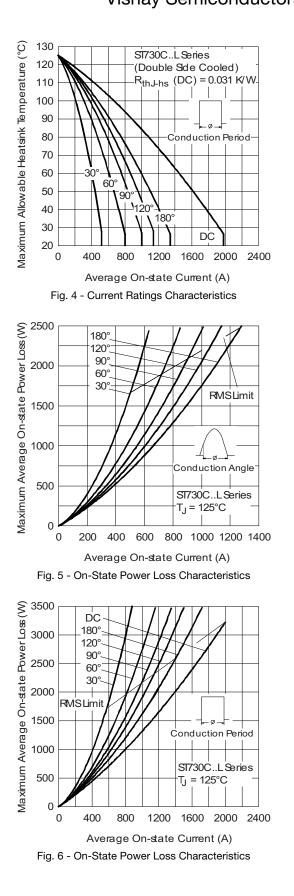












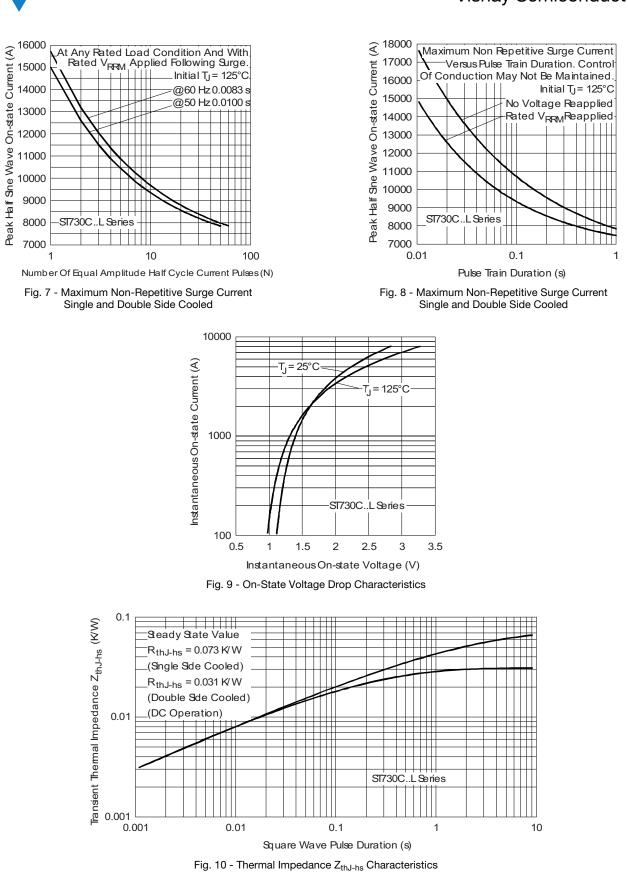
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4

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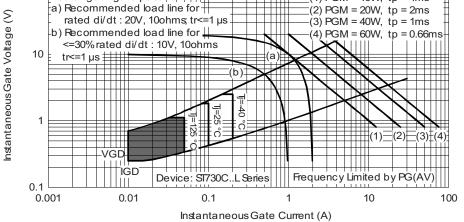


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	ST	73	0	с	20	L	1	-	
	1	2	3	4	5	6	7	8	9	
	1 - 2 -		nay Sen ristor	niconduo	ctors pro	oduct				
	3 - 4 -		•	art numt er grade						
	5 -	C =	0 = converter grade C = ceramic PUK							
	6 - 7 -		Voltage code x 100 = V _{RRM} (see Voltage Ratings table) L = PUK case B-PUK (TO-200AC)							
	8 -		0 = eyelet terminals (gate and auxiliary cathode unsoldered leads) 1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)							
									oldered le	,
				terminal dt: ● No			-		oldered I	eads)
	9 -	Chi			: 1000 V		-			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95076			

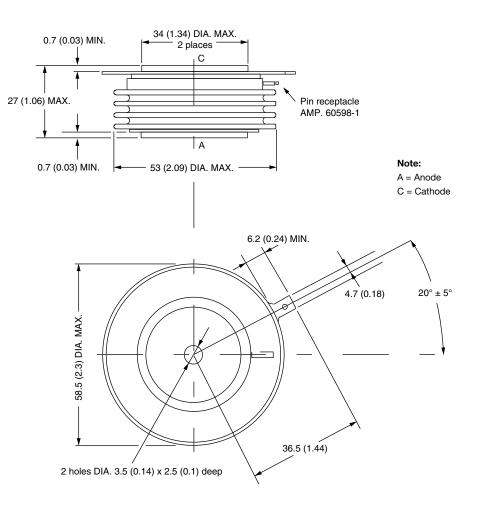
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B-PUK (TO-200AC)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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